Features

- 32K x 8 advanced high-speed CMOS static RAM
- Commercial (0° to 70°C) and Industrial (-40° to 85°C) temperature options
- Equal access and cycle times
 - Commercial: 12ns
 - Commercial and Industrial: 15/20/25ns
- One Chip Select plus one Output Enable pin
- Bidirectional data inputs and outputs directly TTL-compatible
- Low power consumption via chip deselect
- Commercial product available in 28-pin 300-mil Plastic DIP, 300 mil Plastic SOJ and TSOP packages
- Industrial product available in 28-pin 300 mil Plastic SOJ and TSOP packages
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Green parts available, see ordering information

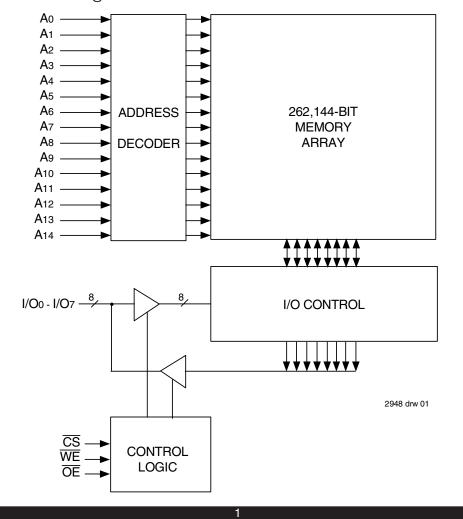
Description

The IDT71256SA is a 262,144-bit high-speed Static RAM organized as $32K \times 8$. It is fabricated using high-performance, high-reliability CMOS technology. This state-of-the-art technology, combined with innovative circuit design techniques, provides a cost-effective solution for high-speed memory needs.

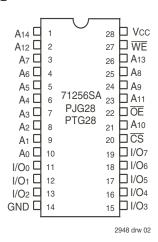
The IDT71256SA has an output enable pin which operates as fast as 6ns, with address access times as fast as 12ns. All bidirectional inputs and outputs of the IDT71256SA are TTL-compatible and operation is from a single 5V supply. Fully static asynchronous circuitry is used, requiring no clocks or refresh for operation.

The IDT71256SA is packaged in 28-pin 300-mil Plastic DIP, 28-pin 300 mil Plastic SOJ and TSOP.

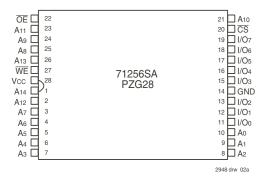
Functional Block Diagram



Pin Configurations(1)



DIP/SOJ Top View



TSOP Top View

NOTE:

1. This text does not indicate orientation of actual part-marking.

Recommended Operating Temperature and Supply Voltage

Grade	Temperature	GND	Vcc
Commercial	0°C to +70°C	0V	4.5V ± 5.5V
Industrial	-40°C to +85°C	0V	4.5V ± 5.5V

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Value	Unit
Vcc	Supply Voltage Relative to GND	-0.5 to +7.0	V
VTERM	Terminal Voltage Relative to GND	-0.5 to Vcc+0.5	V
TBIAS	Temperature Under Bias	-55 to +125	°C
Tstg	Storage Temperature	-55 to +125	°C
Рт	Power Dissipation	1.0	W
Іоит	DC Output Current	50	mA

2948 tbl 02

1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect

Truth Table^(1,2)

<u></u> C S	ŌĒ	WE	I/O	Function
L	L	Н	DATAout	Read Data
L	Х	L	DATAIN	Write Data
L	Н	Н	High-Z	Outputs Disabled
Н	Χ	Χ	High-Z	Deselected - Standby (ISB)
VHC ⁽³⁾	Χ	Χ	High-Z	Deselected - Standby (ISB1)

2948 tbl 03

2948 tbl 04

- 1. $H = V_{IH}$, $L = V_{IL}$, x = Don't care.
- 2. VLC = 0.2V, VHC = VCC -0.2V.
- 3. Other inputs $\geq V_{HC}$ or $\leq V_{LC}$.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	٧
GND	Ground	0	0	0	٧
VIH	Input High Voltage	2.2		Vcc +0.5	٧
VIL	Input Low Voltage	-0.5 ⁽¹⁾		0.8	٧

NOTE:

1. V_{IL} (min.) = -1.5V for pulse width less than 10ns, once per cycle.

DC Electrical Characteristics

 $(VCC = 5.0V \pm 10\%)$

			IDT71256SA		
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
Iu	Input Leakage Current	Vcc = Max., Vin = GND to Vcc	_	5	μΑ
llo	Output Leakage Current	Vcc = Max., \overline{CS} = V _{IH} , Vout = GND to Vcc	_	5	μΑ
Vol	Output Low Voltage	IoL = 8mA, Vcc = Min.	_	0.4	V
Vон	Output High Voltage	IOH = -4mA, VCC = Min.	2.4	-	V

2948 tbl 05

DC Electrical Characteristics(1)

 $(VCC = 5.0V \pm 10\%, VLC = 0.2V, VHC = VCC-0.2V)$

Symbol	Parameter	71256SA12	71256SA15	71256SA20	71256SA25	Unit
Icc	$\frac{\text{Dynamic Operating Current}}{\text{CS}} \leq \text{VIL, Outputs Open, Vcc} = \text{Max., f} = \text{fmax}^{(2)}$	160	150	145	145	mA
ISB	Standby Power Supply Current (TTL Level) $\overline{CS} \ge VH$, Outputs Open, Vcc = Max., f = fmax ⁽²⁾	50	40	40	40	mA
ISB1	Standby Power Supply Current (CMOS Level) $\overline{CS} \ge V$ HC, Outputs Open, V CC = Max., $f = 0^{(2)}$, V IN $\le V$ LC or V IN $\ge V$ HC	15	15	15	15	mA

2948 tbl 06 NOTES:

- 1. All values are maximum guaranteed values.
- 2. $f_{MAX} = 1/t_{RC}$ (all address inputs are cycling at f_{MAX}); f = 0 means no address input lines are changing.

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
AC Test Load	See Figures 1 and 2

Capacitance

 $(TA = +25^{\circ}C, f = 1.0MHz, SOJ package)$

Symbol	Parameter ⁽¹⁾	Conditions	Max.	Unit
Cin	Input Capacitance	VIN = 3dV	7	pF
Cvo	I/O Capacitance	Vout = 3dV	7	pF

NOTE:

2948 tbl 07

1. This parameter is guaranteed by device characterization, but not production tested.

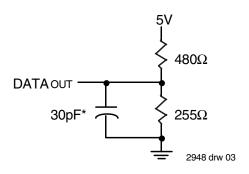


Figure 1. AC Test Load

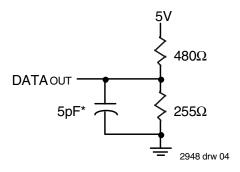


Figure 2. AC Test Load (for tclz, tolz, tchz, tohz, tow, and twhz)

*Including jig and scope capacitance.

AC Electrical Characteristics (Vcc = 5.0V ± 10%)

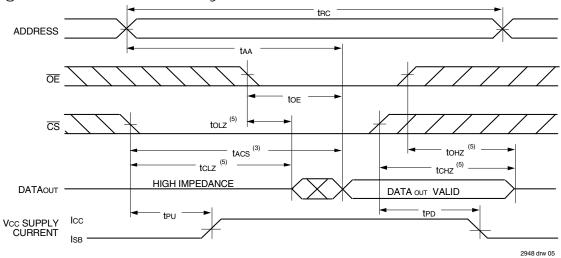
	lectrical characteristics (vi	7125	6SA12	71256SA15 7125		71256	5SA20	7125	6SA25	
Symbol	Parameter	Min.	Max.	Min.	Мах.	Min.	Max.	Min.	Max.	Unit
Read Cy	rcle									
trc	Read Cycle Time	12	_	15		20	_	25	_	ns
taa	Address Access Time		12	_	15	_	20	_	25	ns
tacs	Chip Select Access Time	_	12		15		20		25	ns
tclz ⁽¹⁾	Chip Select to Output in Low-Z	4	_	4		4	_	4	_	ns
tcHz ⁽¹⁾	Chip Select to Output in High-Z	0	6	0	7	0	10	0	11	ns
toe	Output Enable to Output Valid	_	6		7		10	_	11	ns
tolz ⁽¹⁾	Output Enable to Output in Low-Z	0	_	0		0	_	0	_	ns
tонz ⁽¹⁾	Output Disable to Output in High-Z	0	6	0	6	0	8	0	10	ns
tон	Output Hold from Address Change	3	_	3	_	3	_	3	_	ns
tpu ⁽¹⁾	Chip Select to Power Up Time	0	_	0	_	0	_	0	_	ns
tpD ⁽¹⁾	Chip Deselect to Power Down Time	_	12	_	15		20		25	ns
Write Cy	<i>y</i> cle		•		•		•	•		
twc	Write Cycle Time	12	_	15		20	_	25	_	ns
taw	Address Valid to End-of-Write	9	_	10		15	_	20	_	ns
tcw	Chip Select to End-of-Write	9	_	10		15	_	20	_	ns
tas	Address Set-up Time	0	_	0		0	_	0	_	ns
twp	Write Pulse Width	8	_	10		15	_	20	_	ns
twr	Write Recovery Time	0	_	0		0	_	0	_	ns
tow	Data Valid to End-of-Write	6	_	7		11	_	13	_	ns
tон	Data Hold Time	0		0	_	0		0	_	ns
tow ⁽¹⁾	Output Active from End-of-Write	4	_	4		4	_	4	_	ns
twhz ⁽¹⁾	Write Enable to Output in High-Z	0	6	0	6	0	10	0	11	ns

NOTE:

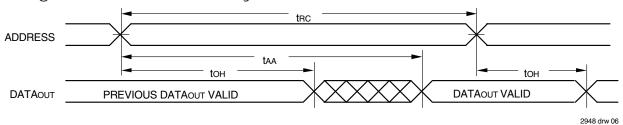
1. This parameter is guaranteed with the AC Load (Figure 2) by device characterization, but is not production tested.

2948 tbl 09

Timing Waveform of Read Cycle No. 1⁽¹⁾



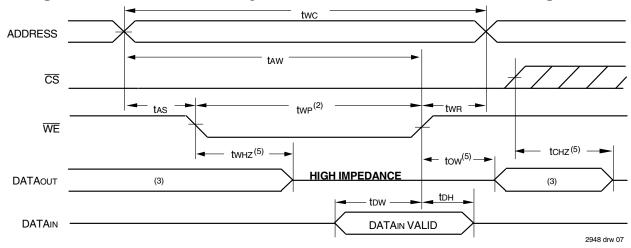
Timing Waveform of Read Cycle No. 2^(1,2,4)



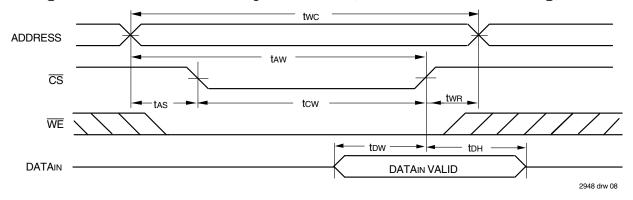
NOTES:

- 1. WE is HIGH for Read Cycle.
- 2. Device is continuously selected, \overline{CS} is LOW.
- 3. Address must be valid prior to or coincident with the later of $\overline{\text{CS}}$ transition LOW; otherwise tax is the limiting parameter.
- 4. $\overline{\mathsf{OE}}$ is LOW.
- 5. Transition is measured ±200mV from steady state.

Timing Waveform of Write Cycle No. 1 (WE Controlled Timing)(1,2,4)



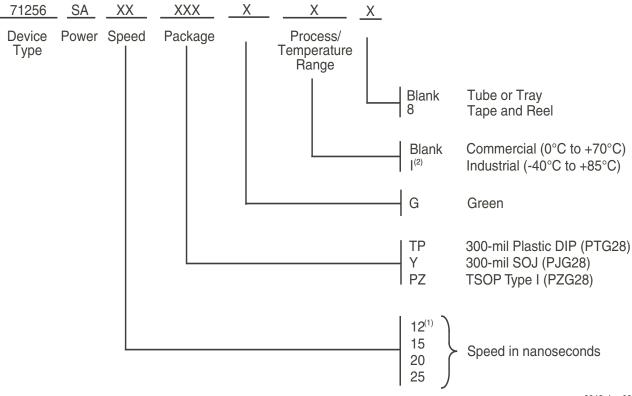
Timing Waveform of Write Cycle No. 2 (CS Controlled Timing)(1,4)



NOTES:

- 1. A write occurs during the overlap of a LOW $\overline{\text{CS}}$ and a LOW $\overline{\text{WE}}.$
- 2. $\overline{\text{OE}}$ is continuously HIGH. If during a $\overline{\text{WE}}$ controlled write cycle $\overline{\text{OE}}$ is LOW, twp must be greater than or equal to twHz + tbw to allow the I/O drivers to turn off and data to be placed on the bus for the required tbw. If $\overline{\text{OE}}$ is HIGH during a $\overline{\text{WE}}$ controlled write cycle, this requirement does not apply and the minimum write pulse is as short as the specified twp.
- 3. During this period, I/O pins are in the output state, and input signals must not be applied.
- 4. If the CS LOW transition occurs simultaneously with or after the WE LOW transition, the outputs remain in a high-impedance state.
- 5. Transition is measured ±200mV from steady state.

Ordering Information



NOTES:

2948 drw 09

- 1. Available in commercial temperature range only.
- 2. Contact your local sales office for Industrial temp range for other speeds, packages and powers.

Orderable Part Information

Speed (ns)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
12	71256SA12PZG	PZG28	TSOP	С
	71256SA12PZG8	PZG28	TSOP	С
	71256SA12TPG	PTG28	PDIP	С
	71256SA12YG	PJG28	SOJ	С
	71256SA12YG8	PJG28	SOJ	С
15	71256SA15PZG	PZG28	TSOP	С
	71256SA15PZG8	PZG28	TSOP	С
	71256SA15PZGI	PZG28	TSOP	I
	71256SA15PZGI8	PZG28	TSOP	I
	71256SA15TPG	PTG28	PDIP	С
	71256SA15TPGI	PTG28	PDIP	I
	71256SA15YG	PJG28	SOJ	С
	71256SA15YG8	PJG28	SOJ	С
	71256SA15YGI	PJG28	SOJ	I
	71256SA15YGl8	PJG28	SOJ	I

Speed (ns)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
20	71256SA20PZG	PZG28	TSOP	С
	71256SA20PZG8	PZG28	TSOP	С
	71256SA20PZGI	PZG28	TSOP	ı
	71256SA20PZGI8	PZG28	TSOP	- 1
	71256SA20TPG	PTG28	PDIP	С
	71256SA20TPGI	PTG28	PDIP	I
	71256SA20YG	PJG28	SOJ	С
	71256SA20YG8	PJG28	SOJ	С
	71256SA20YGI	PJG28	SOJ	ı
	71256SA20YGl8	PJG28	SOJ	I
25	71256SA25PZG	PZG28	TSOP	С
	71256SA25PZG8	PZG28	TSOP	С
	71256SA25PZGI	PZG28	TSOP	ı
	71256SA25PZGI8	PZG28	TSOP	- 1
	71256SA25TPG	PTG28	PDIP	С
	71256SA25TPGI	PTG28	PDIP	I
	71256SA25YG	PJG28	SOJ	С
	71256SA25YG8	PJG28	SOJ	С

Datasheet Document History

1/7/00		Updated to new format
	Pg. 1, 3, 4, 7	Revised Industrial Temperature range offerings
	Pg. 6	Removed Note No. 1 for Write Cycle diagrams, renumbered footnotes and notes
	Pg. 8	Added Datasheet Document History
08/09/00		Not recommended for new designs
02/01/01		Removed "Not recommended for new designs"
09/30/04	Pg. 7	Added "Restricted hazardous substance device" to ordering informations.
02/20/07	Pg. 7	Added TT generation die step to data sheet ordering information.
04/28/11	Pg. 1, 2, 7	Obsoleted 28-pin 600 mil and removed TT generation die step from Ordering information.
		Added Tape and Reel to Ordering information and updated description of Restricted
		hazardous substance device to Green
11/03/14	Pg. 1 & 8	Removed 12ns I-temp offering in Features. Added note regarding 12ns commercial only on
		the Ordering information page. Removed IDT as a reference for fabrication in Description.
	Pg. 2 & 8	Removed package extensions from pinouts and from Ordering information.
06/29/20	Pg. 1 - 9	Rebranded as Renesas datasheet
	Pg. 1 & 7	Updated Industrial temp range and green availability
	Pg. 2 & 7	Updated package codes
	Pg. 7	Added Orderable Part Information tables

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IS66WVE2M16ECLL-70BLI IS66WVE4M16EALL-70BLI IS61WV102416DBLL-10TLI CY7C1381KV33-100AXC CY7C1381KVE33133AXI 8602501XA 5962-3829425MUA 5962-3829430MUA 5962-8866201YA 5962-8866204TA 5962-9062007MXA 59629161705MXA GS882Z18CD-150I 8413202RA 5962-8866208YA 5962-8866203YA IS61WV102416DBLL-10BLI IS66WVC2M16ECLL7010BLI CY7C1380KV33-250AXC AS6C8016-55BINTR GS81284Z18B-250I AS7C34096B-10TIN GS84018CB-200I
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